Silicon PNP Power Transistors 2SA1094

DESCRIPTION

·With MT-200 package

·Complement to type 2SC2564

APPLICATIONS

·For power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

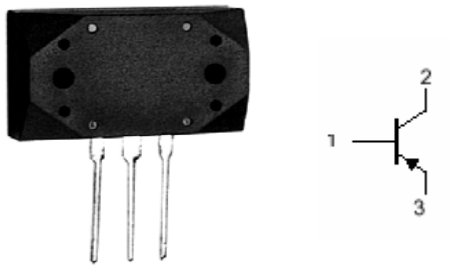

Fig.1 simplified outline (MT-200) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-140	V
V_{CEO}	Collector-emitter voltage	Open base	-140	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-12	A
I_B	Base current		-1.2	A
P_C	Collector power dissipation	T_C=25□	120	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-0.1A ; I_B=0	-140			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-0.01A ; I_C=0	-5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-5A ;I_B=-0.5A			-2.0	V
V_{BE}	Base-emitter on voltage	I_C=-5A ; V_{CE}=-5V			-2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-140V; I_E=0			-50	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-50	μA
h_{FE-1}	DC current gain	I_C=-1A ; V_{CE}=-5V	55		240	
h_{FE-2}	DC current gain	I_C=-5A ; V_{CE}=-5V	30			
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=-10V;f=1MHz		220		pF
f_T	Transition frequency	I_C=-1A ; V_{CE}=-10V		70		MHz

◆ **h_{FE-1} classifications**

R	O	Y
55-110	80-160	120-240

PACKAGE OUTLINE

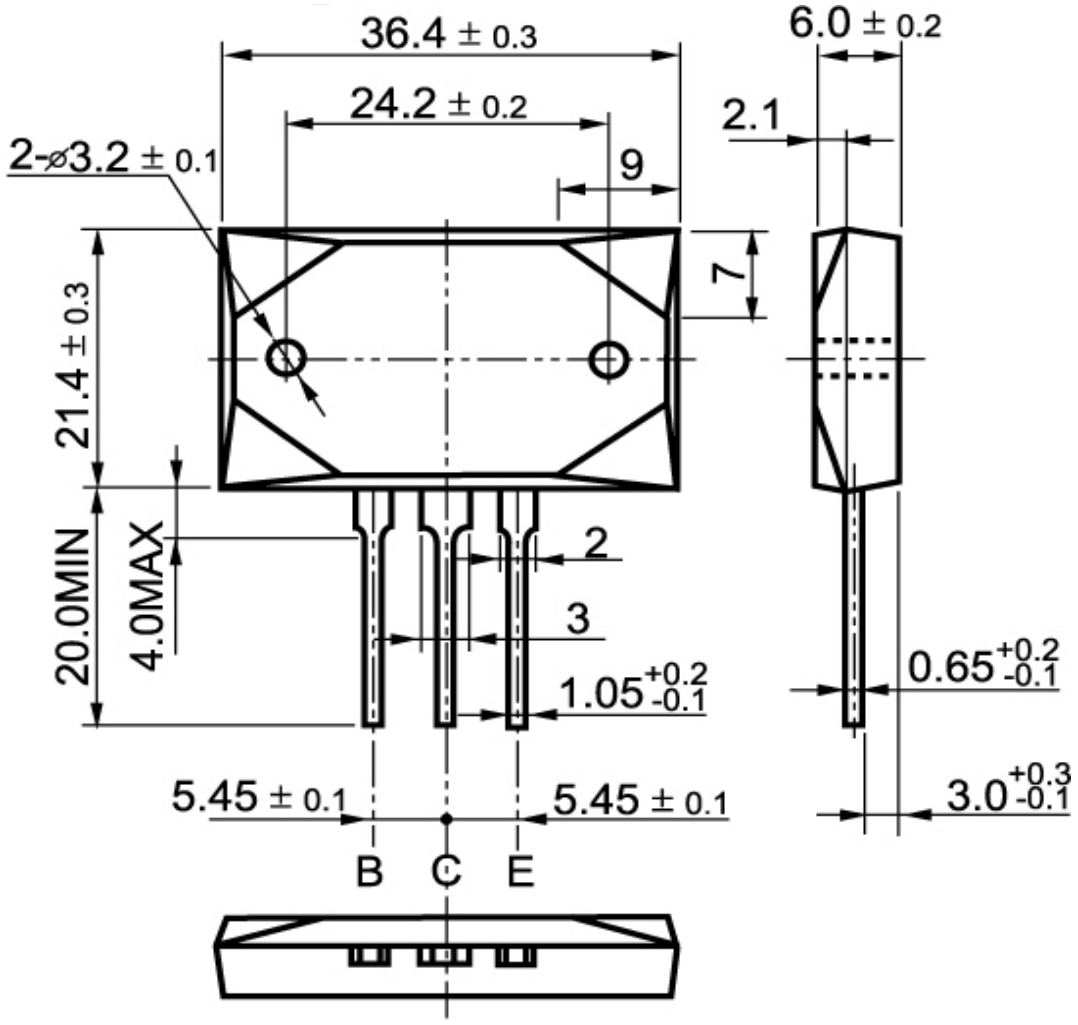

Fig.2 outline dimensions